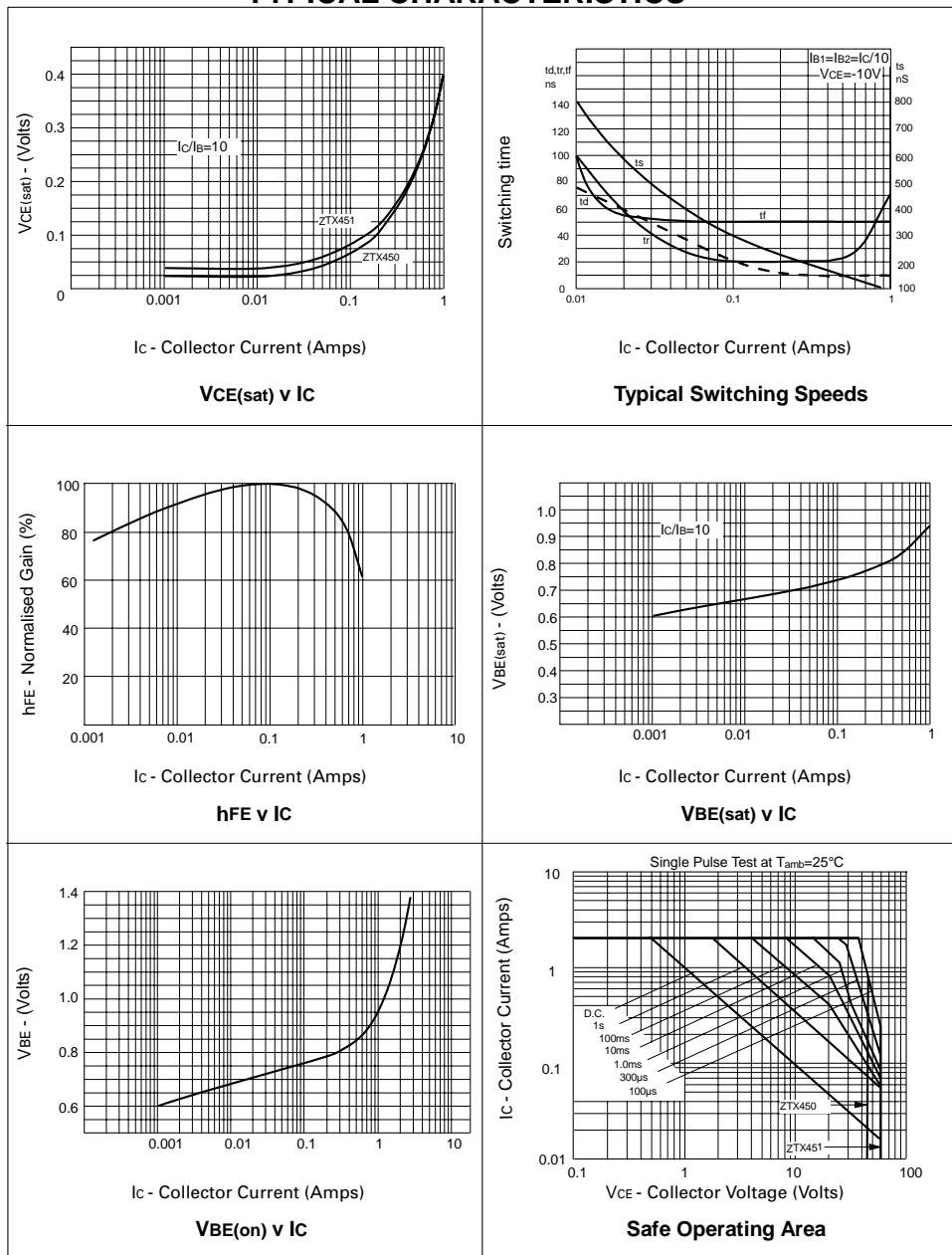


ZTX450
ZTX451

TYPICAL CHARACTERISTICS



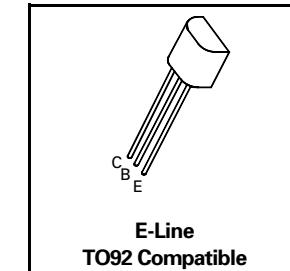
NPN SILICON PLANAR MEDIUM POWER TRANSISTORS

ISSUE 2 - MARCH 1994

FEATURES

- * 60 Volt V_{CEO}
- * 1 Amp continuous current
- * P_{tot} = 1 Watt

ZTX450
ZTX451



ABSOLUTE MAXIMUM RATINGS.

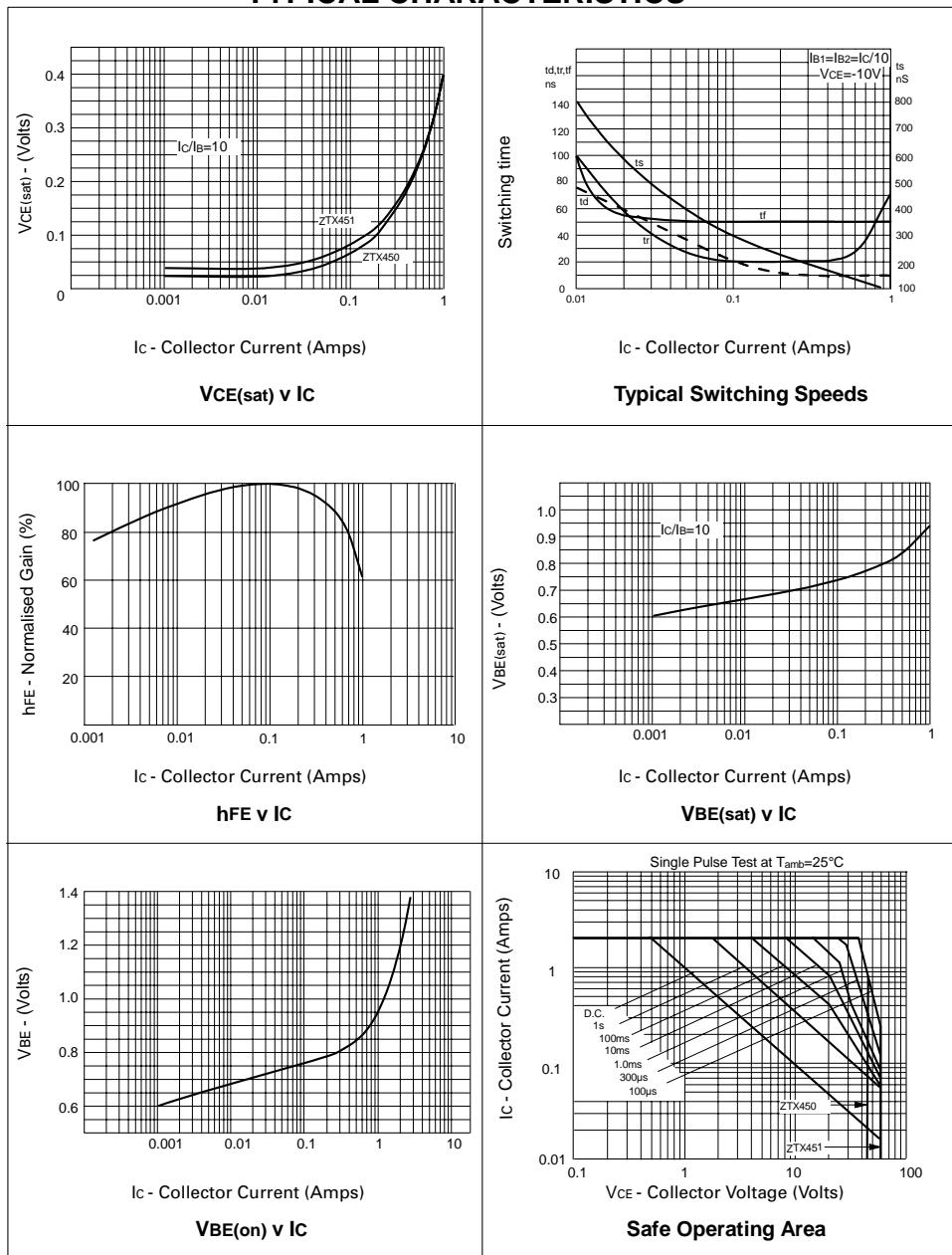
PARAMETER	SYMBOL	ZTX450	ZTX451	UNIT
Collector-Base Voltage	V _{CBO}	60	80	V
Collector-Emitter Voltage	V _{CEO}	45	60	V
Emitter-Base Voltage	V _{EBO}		5	V
Peak Pulse Current	I _{CM}		2	A
Continuous Collector Current	I _C		1	A
Power Dissipation at T _{amb} =25°C	P _{tot}		1	W
Operating and Storage Temperature Range	T _j ;T _{stg}		-55 to +200	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	ZTX450		ZTX451		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60		80		V	I _C =100µA
Collector-Emitter Sustaining Voltage	V _{CEO(sus)}	45		60		V	I _C =10mA*
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5		5		V	I _E =100µA
Collector Cut-Off Current	I _{CBO}			0.1	0.1	µA	V _{CB} =45V V _{CB} =60V
Emitter Cut-Off Current	I _{EBO}			0.1	0.1	µA	V _{EB} =4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.25	0.35	V	I _C =150mA, I _B =15mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}			1.1	1.1	V	I _C =150mA, I _B =15mA*
Static Forward Current Transfer Ratio	h _{FE}	100 15	300	50 10	150		I _C =150mA, V _{CE} =10V* I _C =1A, V _{CE} =10V*
Transition Frequency	f _T	150		150		MHz	I _C =50mA, V _{CE} =10V f=100MHz
Output Capacitance	C _{obo}			15	15	pF	V _{CB} =10V, f=1MHz

ZTX450
ZTX451

TYPICAL CHARACTERISTICS



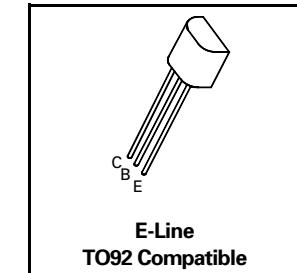
NPN SILICON PLANAR MEDIUM POWER TRANSISTORS

ISSUE 2 - MARCH 1994

FEATURES

- * 60 Volt V_{CEO}
- * 1 Amp continuous current
- * P_{tot} = 1 Watt

ZTX450
ZTX451



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX450	ZTX451	UNIT
Collector-Base Voltage	V _{CBO}	60	80	V
Collector-Emitter Voltage	V _{CEO}	45	60	V
Emitter-Base Voltage	V _{EBO}		5	V
Peak Pulse Current	I _{CM}		2	A
Continuous Collector Current	I _C		1	A
Power Dissipation at T _{amb} =25°C	P _{tot}		1	W
Operating and Storage Temperature Range	T _j ;T _{stg}	-55 to +200		°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	ZTX450		ZTX451		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60		80		V	I _C =100µA
Collector-Emitter Sustaining Voltage	V _{CEO(sus)}	45		60		V	I _C =10mA*
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5		5		V	I _E =100µA
Collector Cut-Off Current	I _{CBO}			0.1	0.1	µA	V _{CB} =45V V _{CB} =60V
Emitter Cut-Off Current	I _{EBO}			0.1	0.1	µA	V _{EB} =4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.25	0.35	V	I _C =150mA, I _B =15mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}			1.1	1.1	V	I _C =150mA, I _B =15mA*
Static Forward Current Transfer Ratio	h _{FE}	100 15	300	50 10	150		I _C =150mA, V _{CE} =10V* I _C =1A, V _{CE} =10V*
Transition Frequency	f _T	150		150		MHz	I _C =50mA, V _{CE} =10V f=100MHz
Output Capacitance	C _{obo}			15	15	pF	V _{CB} =10V, f=1MHz

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [BC546/116](#) [BC557/116](#) [BSW67A](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE63](#) [C4460](#) [2SA1419T-TD-H](#)
[2SA1721-O\(TE85L,F\)](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [2SC5488A-TL-H](#) [2SD2150T100R](#) [SP000011176](#) [2N2369ADCSM](#) [2SC2412KT146S](#)
[2SC5490A-TL-H](#) [2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [US6T6TR](#) [732314D](#) [CMXT3906 TR](#)
[CPH3121-TL-E](#) [CPH6021-TL-H](#) [873787E](#) [UMX21NTR](#) [EMT2T2R](#) [MCH6102-TL-E](#) [FP204-TL-E](#) [NJL0302DG](#) [2N3583](#) [2SA1434-TB-E](#)
[2SC3143-4-TB-E](#) [2SD1621S-TD-E](#) [30A02MH-TL-E](#) [NSV40301MZ4T1G](#) [NTE13](#) [NTE15](#) [NTE16001](#) [NTE16006](#) [NTE26](#) [NTE320](#)
[NTE323](#)